

## Elastic Constants for Isotropic Materials (ctnd.) • Now consider a three dimensional object subjected to a uniaxial stress $\sigma_x$ . • In this case, the dimensions of the deformed volume element are: $\begin{aligned} &\Delta x \to \Delta x (1 + \varepsilon_x) \\ &\Delta y \to \Delta y (1 - \upsilon \varepsilon_x) \\ &\Delta z \to \Delta z (1 - \upsilon \varepsilon_x) \end{aligned}$ • Thus the change in volume $\Delta V$ is: $\begin{aligned} &\Delta V = \Delta x \Delta y \Delta z (1 - 2\upsilon) \varepsilon_x \end{aligned}$ • For small strain (i.e. neglecting terms in $\varepsilon_x^2$ ), we get

$$\Delta \mathbf{V} = \Delta \mathbf{x} \Delta \mathbf{y} \Delta \mathbf{z} (1 + \mathbf{\varepsilon}_{r}) (1 - \mathbf{\upsilon} \mathbf{\varepsilon}_{r})^{2} - \Delta \mathbf{x} \Delta \mathbf{y} \Delta \mathbf{z}$$

• Thus for v = 0.5, there is no change in volume taking place.

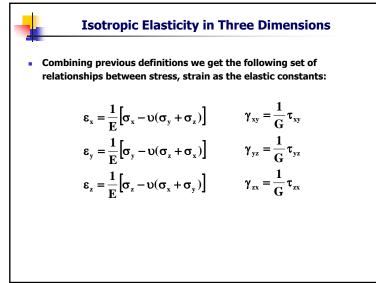
## Elastic Constants for Isotropic Materials (ctnd.)

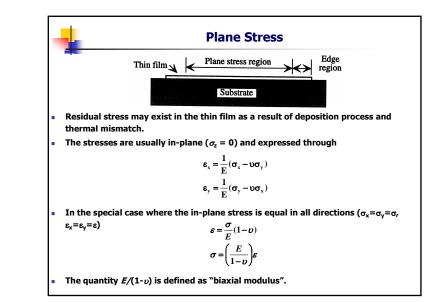
- Shear Modulus
- There is also a linear relation between shear stress and resulting shear strain written in terms of the shear modulus noted by G.

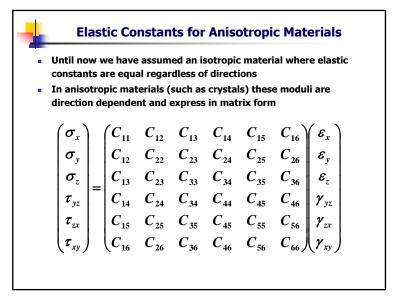
$$\tau_{xy} = G_{xy}\gamma_{xy}$$

• It can be shown that this quantity is related to Young's modulus and Poisson ration through:

$$G = \frac{E}{2(1+v)}$$







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<ul> <li>In the case of cubic crystals this matrix only contains three independent quantities and reduces to</li> </ul>								
		$C_{11}$	$C_{12}$	<i>C</i> <sub>12</sub>	0	0 0 0 C <sub>44</sub> 0	0`	)
		$C_{12}$	<i>C</i> <sub>11</sub>	$C_{12}$	0	0	0	
		$C_{12}$	$C_{12}$	<i>C</i> <sub>11</sub>	0	0	0	
		0	0	0	C <sub>44</sub>	0	0	
		0	0	0	0	$C_{44}$	0	
		0	0	0	0	0	C <sub>44</sub>	)
<ul> <li>where C<sub>ii</sub> are stiffness coefficients. For silicon:</li> </ul>								
$C_{11} = 166  GPa$								
$C_{12} = 64 GPa$								
• In a more compact notation: $C_{44} = 80 GPa$								
$\sigma_1 = \sum_{j} C_{11} \varepsilon_j$								
$\sigma_{I} = \sum_{J} C_{IJ} \varepsilon_{J}$ $\varepsilon_{I} = \sum_{J} S_{IJ} \sigma_{J}$								
					-			



- Thermal expansion refers to the tendency of free bodies to expand when heated.
- The linear thermal expansion coefficient is defined as:

$$\alpha_{\rm T} = \frac{{\rm d}\epsilon_{\rm x}}{{\rm d}{\rm T}}$$

- where T is temperature.
- The units for  $\alpha_T$  are K<sup>-1</sup> and tends to be in the 10<sup>-6</sup> to 10<sup>-7</sup> range.
- We write:

$$\varepsilon_{x}(T) = \varepsilon_{x}(T_{0}) + \alpha_{T}\Delta T$$
 where  $\Delta T = T - T_{0}$ 

Consider a thin film deposited onto a substrate at a deposition temperature T<sub>d</sub> Assume the film is stress free at that temperature. The sample is then cooled down to room temperature T<sub>r</sub>. Since substrate is much thicker than film it will contract according to its own thermal expansion coefficient and force the thin film to contract with it.

• Thermal Expansion and Thin-Film Stress (ctnd.)  
• The thermal strain in the substrate (in one in-plane dimension) is:  

$$\varepsilon_s = -\alpha_{Ts}\Delta T$$
  
where:  
 $\Delta T = T_d - T_c$   
• If the thin film were not attached to the substrate it would experience a thermal strain given by:  
 $\varepsilon_{r,tree} = -\alpha_{Tr}\Delta T$   
• However, because it is attached the actual strain in the film must be equal to that of the substrate:  
 $\varepsilon_{r,attached} = -\alpha_{Ts}\Delta T$   
• The thermal mismatch strain is given by:  
 $\varepsilon_{r,mismatch} = \varepsilon_{r,attached} - \varepsilon_{r,free} = (\alpha_{TT} - \alpha_{Ts})\Delta T$   
the film will therefore develop a bi-axial residual stress of:  
 $\sigma_{r,residual} = \left(\frac{E}{1-\upsilon}\right)\varepsilon_{r,mismatch}$ 

